

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Rating	Unit
V _{DSS}	Drain-Source Voltage		-20	V
V _{GSS}	Gate-Source Voltage		±10	
I _D *	Continuous Drain Current	V _{GS} =-4.5V	-3	A
I _{DM} *	300μs Pulsed Drain Current		-12	
I _S *	Diode Continuous Forward Current		-1	A
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
P _D *	Power Dissipation for Single Operation	T _A =25°C	1.47	W
		T _A =100°C	0.58	
R _{θJA} *	Thermal Resistance-Junction to Ambient		85	°C/W

Note:

*Surface Mounted on 1in² pad area, $t \leq 10\text{sec}$.
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	APM2095PD			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-12V, V _{GS} =0V			-1	μA
		T _J =85°C			-30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-0.5	-0.7	-1	V
I _{GSS}	Gate Leakage Current	V _{GS} =±10V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^a	Drain-Source On-state Resistance	V _{GS} =-4.5V, I _{DS} =-3A		75	100	mΩ
		V _{GS} =-2.5V, I _{DS} =-1.5A		100	130	
V _{SD} ^a	Diode Forward Voltage	I _{SD} =-0.5A , V _{GS} =0V		-0.7	-1.3	V
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =-10V, V _{GS} =-4.5V, I _{DS} =-3A		11.5	15	nC
Q _{gs}	Gate-Source Charge			1.7		
Q _{gd}	Gate-Drain Charge			1.8		

Electrical Characteristics (Cont.) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

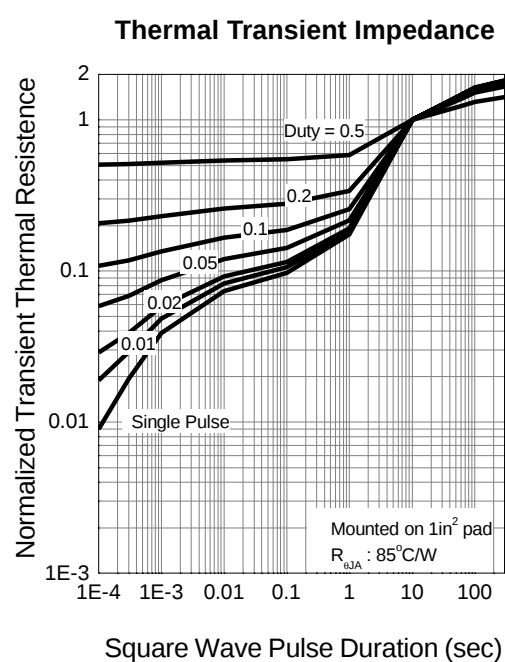
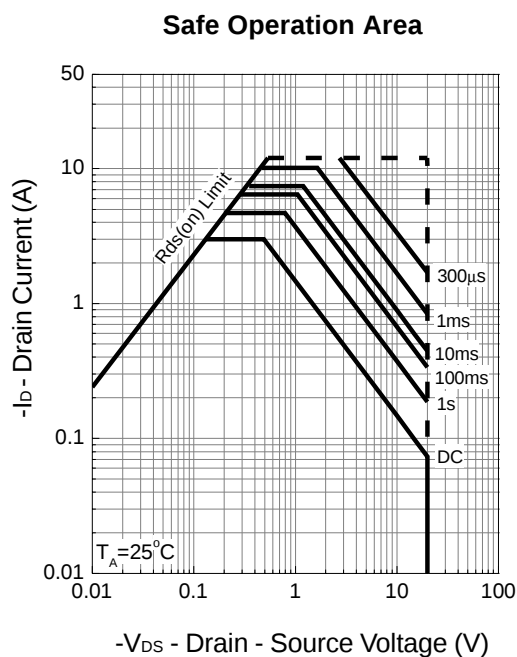
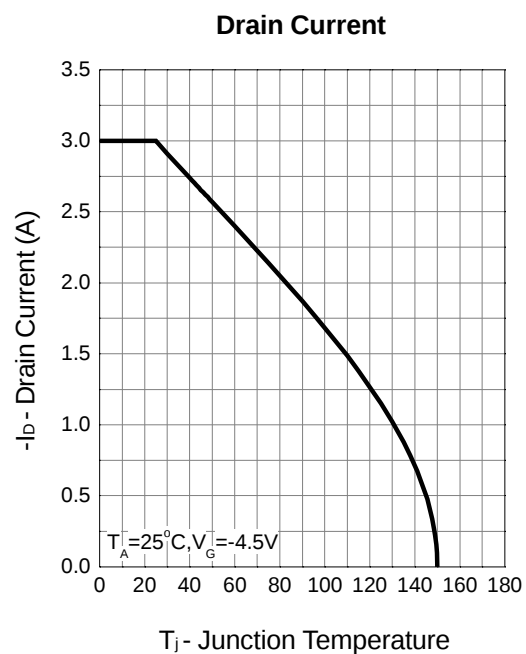
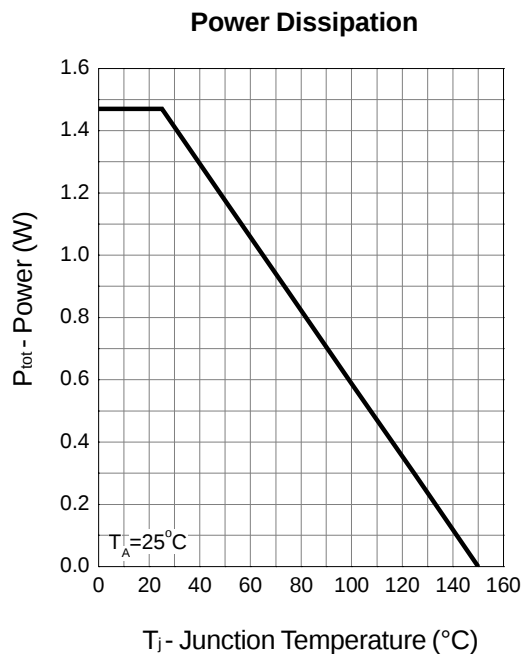
Symbol	Parameter	Test Condition	APM2095PD			Unit
			Min.	Typ.	Max.	
Dynamic Characteristics ^b						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz		12.5		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-15V, Frequency=1.0MHz		1160		pF
C _{oss}	Output Capacitance			250		
C _{rss}	Reverse Transfer Capacitance			85		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-10V, R _L =10Ω, I _{DS} =-1A, V _{GEN} =-4.5V, R _G =6Ω		12	21	ns
T _r	Turn-on Rise Time			25	42	
t _{d(OFF)}	Turn-off Delay Time			52	85	
T _f	Turn-off Fall Time			18	32	

Notes:

a : Pulse test ; pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

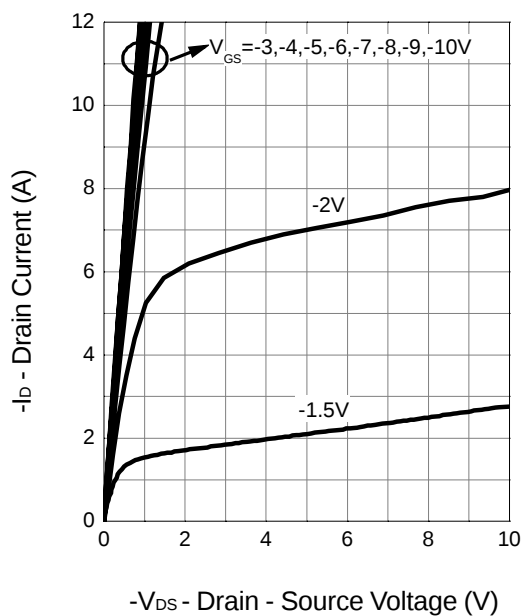
b : Guaranteed by design, not subject to production testing.

Typical Characteristics

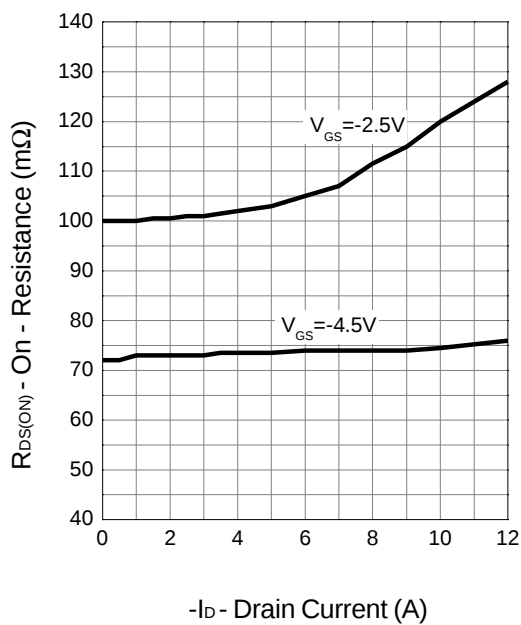


Typical Characteristics (Cont.)

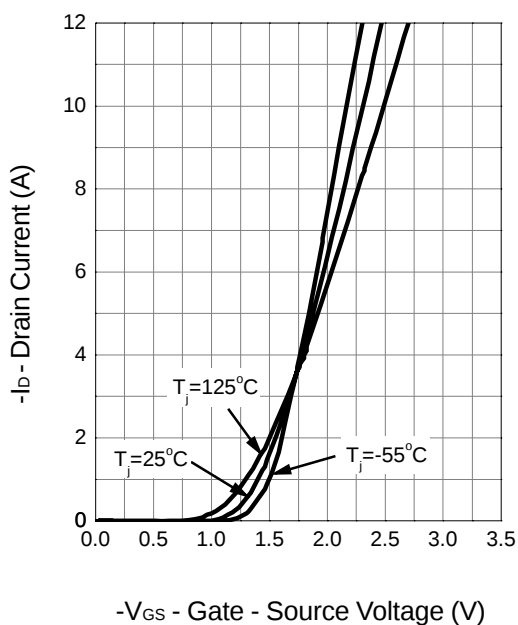
Output Characteristics



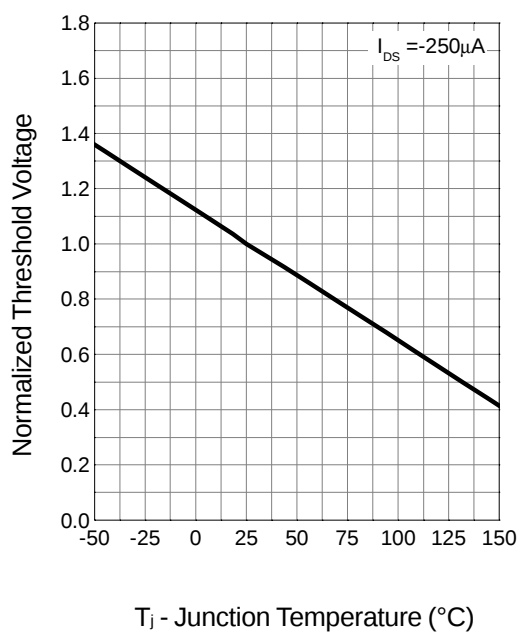
Drain-Source On Resistance



Transfer Characteristics

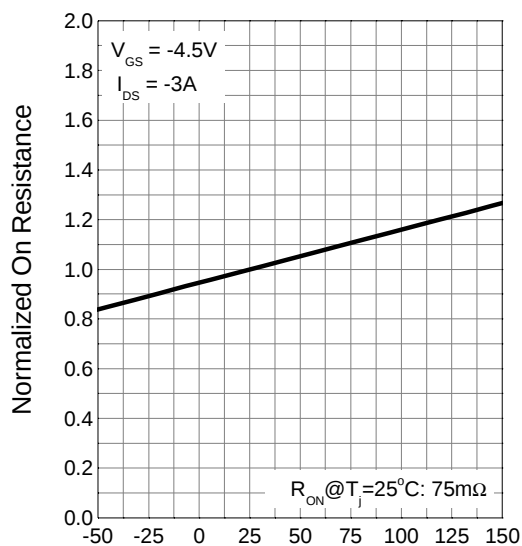


Gate Threshold Voltage



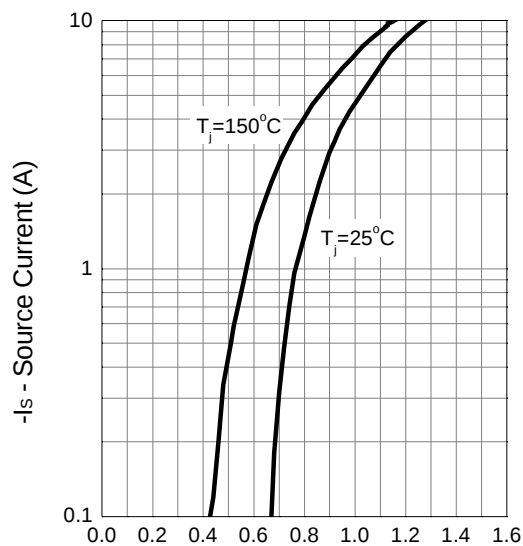
Typical Characteristics (Cont.)

Drain-Source On Resistance



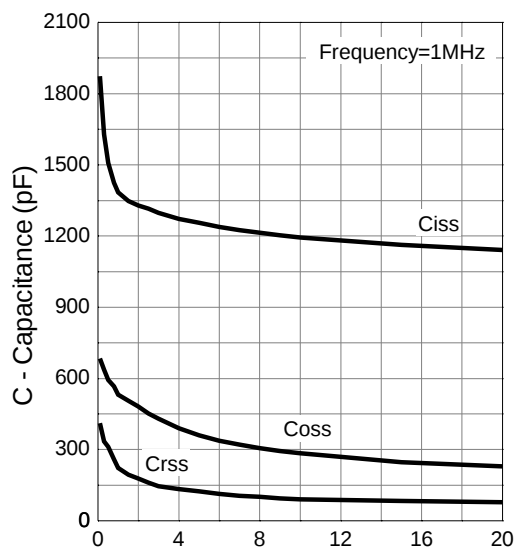
T_j - Junction Temperature ($^{\circ}\text{C}$)

Source-Drain Diode Forward



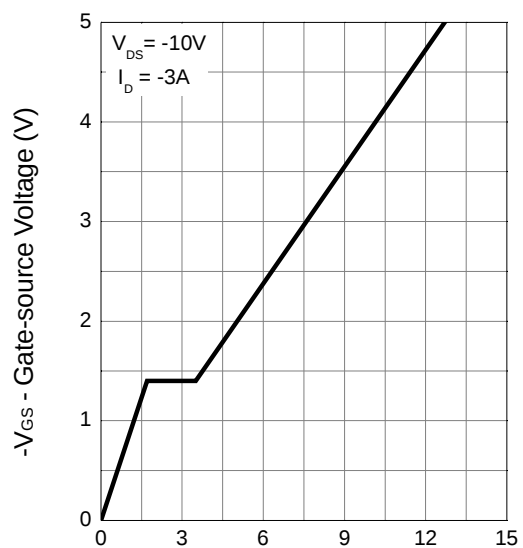
$-V_{SD}$ - Source - Drain Voltage (V)

Capacitance



$-V_{DS}$ - Drain-Source Voltage (V)

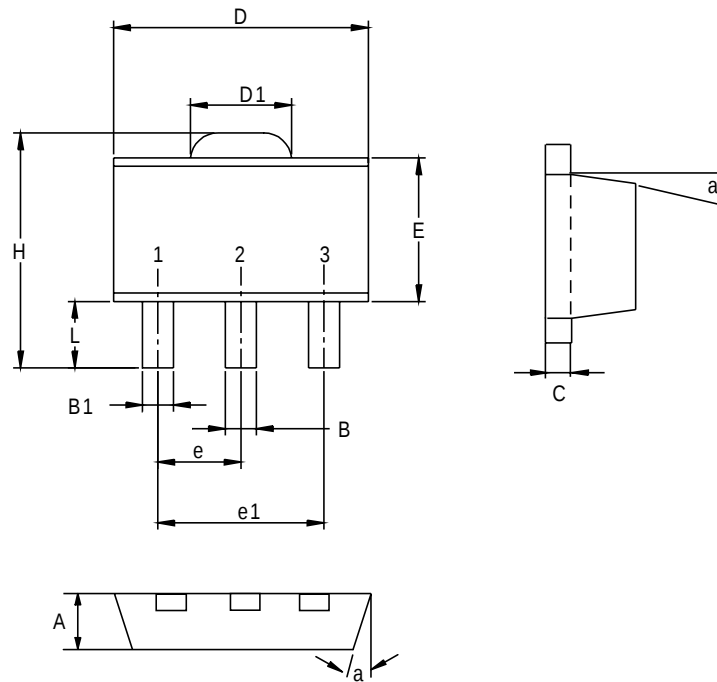
Gate Charge



Q_G - Gate Charge (nC)

Package Information

SOT-89 (Reference EIAJ ED-7500A Registration SC-62)

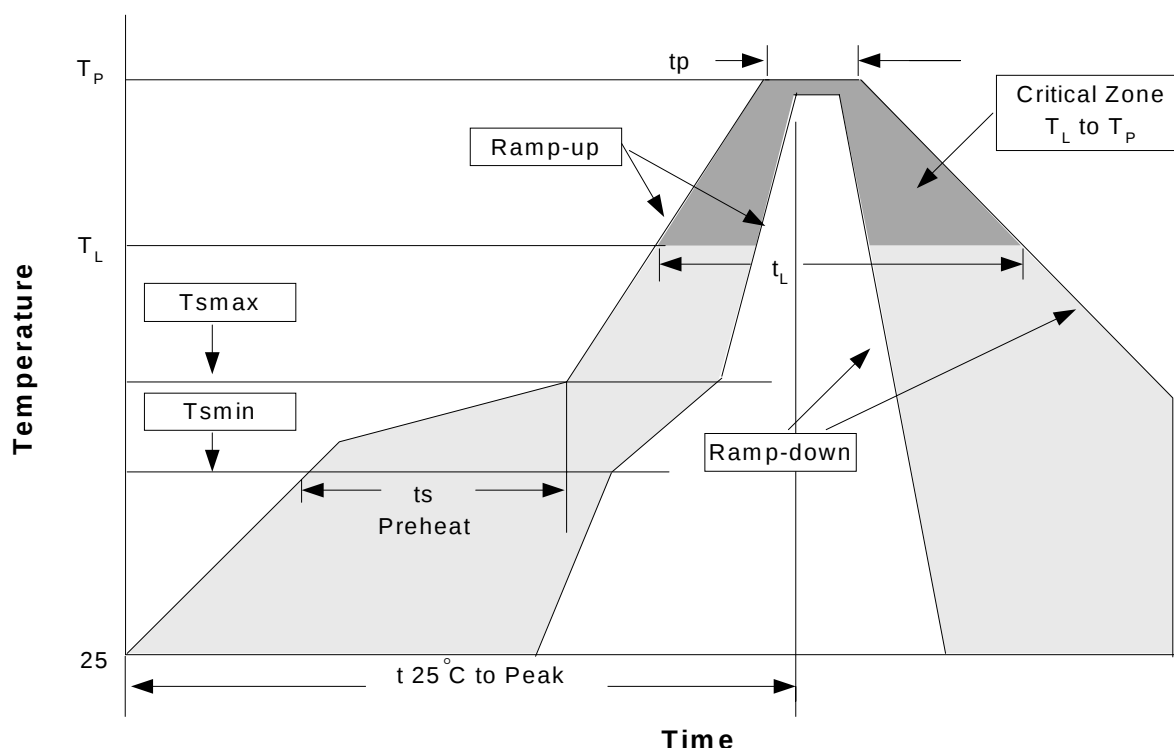


Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	1.40	1.60	0.055	0.063
B	0.40	0.56	0.016	0.022
B1	0.35	0.48	0.014	0.019
C	0.35	0.44	0.014	0.017
D	4.40	4.60	0.173	0.181
D1	1.35	1.83	0.053	0.072
e	1.50 BSC		0.059 BSC	
e1	3.00 BSC		0.118 BSC	
E	2.29	2.60	0.090	0.102
H	3.75	4.25	0.148	0.167
L	0.80	1.20	0.031	0.047
α		10°		10°

Physical Specifications

Terminal Material	Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb), 100%Sn
Lead Solderability	Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3.

Reflow Condition (IR/Convection or VPR Reflow)



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	3°C/second max.	3°C/second max.
Preheat - Temperature Min (T_{smin}) - Temperature Max (T_{smax}) - Time (min to max) (t_s)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: - Temperature (T_L) - Time (t_L)	183°C 60-150 seconds	217°C 60-150 seconds
Peak/Classification Temperature (T_P)	See table 1	See table 2
Time within 5°C of actual Peak Temperature (t_p)	10-30 seconds	20-40 seconds
Ramp-down Rate	6°C/second max.	6°C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

Notes: All temperatures refer to topside of the package .Measured on the body surface.

Classification Reflow Profiles(Cont.)

Table 1. SnPb Eutectic Process – Package Peak Reflow Temperatures

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	240 +0/-5°C	225 +0/-5°C
≥2.5 mm	225 +0/-5°C	225 +0/-5°C

Table 2. Pb-free Process – Package Classification Reflow Temperatures

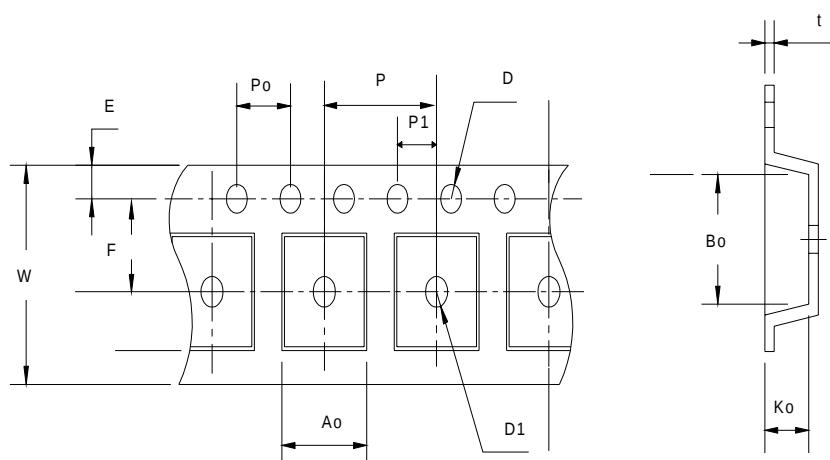
Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 +0°C*	260 +0°C*	260 +0°C*
1.6 mm – 2.5 mm	260 +0°C*	250 +0°C*	245 +0°C*
≥2.5 mm	250 +0°C*	245 +0°C*	245 +0°C*

*Tolerance: The device manufacturer/supplier **shall** assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0°C. For example 260°C+0°C) at the rated MSL level.

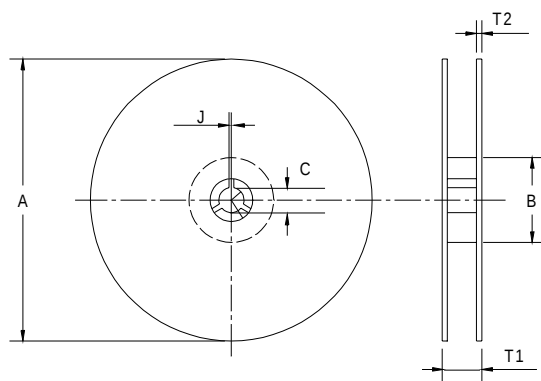
Reliability test program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C, 5 SEC
HOLT	MIL-STD-883D-1005.7	1000 Hrs Bias @125°C
PCT	JESD-22-B,A102	168 Hrs, 100%RH, 121°C
TST	MIL-STD-883D-1011.9	-65°C~150°C, 200 Cycles

Carrier Tape & Reel Dimensions



Carrier Tape & Reel Dimensions(Cont.)



Application	A	B	C	J	T1	T2	W	P	E
SOT-89	178 ±1	70 ± 2	13.5 ± 0.15	3 ± 0.15	14 ± 2	1.3 ± 0.3	12 + 0.3 12 - 0.1	8 ± 0.1	1.75± 0.1
	F	D	D1	Po	P1	Ao	Bo	Ko	t
	5.5 ± 0.05	1.5± 0.1	1.5± 0.1	4.0 ± 0.1	2.0 ± 0.1	4.8 ± 0.1	4.5± 0.1	1.80± 0.1	0.3±0.013

(mm)

Cover Tape Dimensions

Application	Carrier Width	Cover Tape Width	Devices Per Reel
SOT-89	12	9.3	1000

Customer Service

Anpec Electronics Corp.

Head Office :

5F, No. 2 Li-Hsin Road, SBIP,

Hsin-Chu, Taiwan, R.O.C.

Tel : 886-3-5642000

Fax : 886-3-5642050

Taipei Branch :

7F, No. 137, Lane 235, Pac Chiao Rd.,

Hsin Tien City, Taipei Hsien, Taiwan, R. O. C.

Tel : 886-2-89191368

Fax : 886-2-89191369